UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO. : 6,849,493 B2
DATED : February 1, 2005
INVENTOR(S) : Shubneesh Batra et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 1,
Line 37, replace "a is semiconductive wafer fragment **10** is shown at a" with
-- a semiconductive wafer fragment **10** is shown at a --.

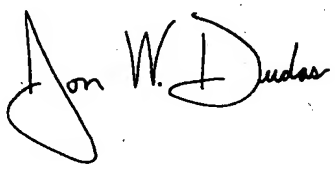
Column 2,
Line 30, replace "**52, 54, 56** and **58** within openings **22, 24, 26, 29** and **30**," with
-- **52, 54, 56** and **58** within openings **22, 24, 26, 28** and **30**, --.

Column 7,
Line 65, replace "layer joining the upper layer at an interlace, the" with
-- layer joining the upper layer at an interface, the --.

Column 8,
Line 61, replace "interlace is elevationally proximate the uppermost surface of" with
-- interface is elevationally proximate the uppermost surface of --.

Signed and Sealed this

Twenty-eighth Day of March, 2006



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